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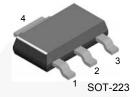


October 2014

FJT44 NPN Epitaxial Silicon Transistor

Features

· High-Voltage Transistor



1. Base 2,4. Collector 3. Emitter

Ordering Information

Part Number	Marking	Package	Packing Method, Size	
FJT44TF	FJT44	SOT-223 4L	Tape and Reel, 4000 pcs	
FJT44KTF	FJT44	SOT-223 4L	Tape and Reel, 2500 pcs	

Absolute Maximum Ratings(1),(2)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	500	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current	300	mA
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C

Notes

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

Thermal Characteristics(3)

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Max.	Unit
P _D	Power Dissipation, T _C = 25°C	2	W
	Derate Above 25°C	16	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

Note:

3. Device is mounted on FR-4 PCB 36 mm × 18 mm × 1.5 mm; mounting pad for the collector lead minimum 6 cm².

Electrical Characteristics(4)

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 100 μA, I _E = 0	500			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 1 \text{ mA}, I_B = 0$	400			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 100 μA, I _C = 0	6			V
I _{CBO}	Collector-Base Cut-Off Current	V _{CB} = 400 V, I _E = 0			100	nA
I _{CES}	Collector-Emitter Cut-Off Current	V _{CE} = 400 V, V _{BE} = 0			500	nA
I _{EBO}	Emitter-Base Cut-Off Current	$V_{EB} = 4 \text{ V}, I_{C} = 0$			100	nA
	DC Current Gain	$V_{CE} = 10 \text{ V, } I_{C} = 1 \text{ mA}$	40			
h _{FE}		V _{CE} = 10 V, I _C = 10 mA	50		200	
		V_{CE} = 10 V, I_{C} = 50 mA	45			
		V_{CE} = 10 V, I_{C} = 100 mA	40			
		$I_C = 1 \text{ mA}, I_B = 0.1 \text{ mA}$			0.40	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 10 mA, I _B = 1 mA			0.50	V
		I _C = 50 mA, I _B = 5 mA			0.75	
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 10 mA, I _B = 1 mA		A	0.75	V
C _{obo}	Output Capacitance	V _{CB} = 20 V, I _E = 0, f = 1.0 MHz			7	pF

Note:

4. Pulse test: pulse width \leq 300 μ s, duty cycle \leq 2.0%

Typical Performance Characteristics

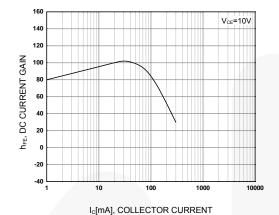


Figure 1. DC Current Gain

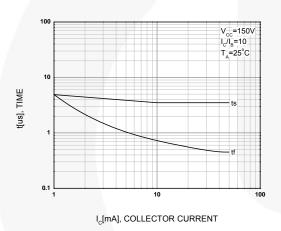


Figure 3. Turn-Off Switching Times

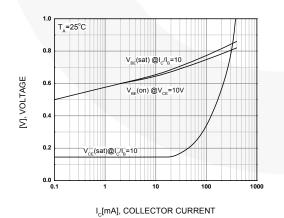


Figure 5. On Voltage

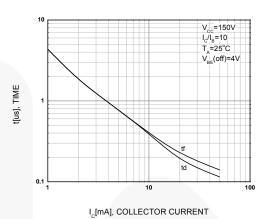


Figure 2. Turn-On Switching Times

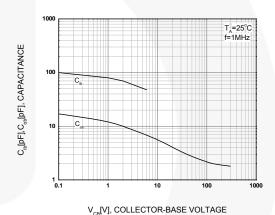


Figure 4. Capacitance

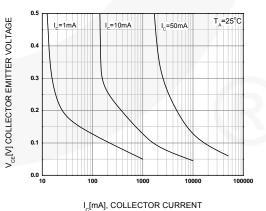


Figure 6. Collector Saturation Region

Typical Performance Characteristics (Continued)

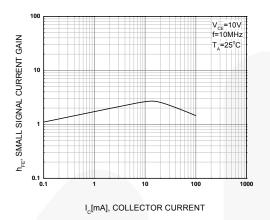
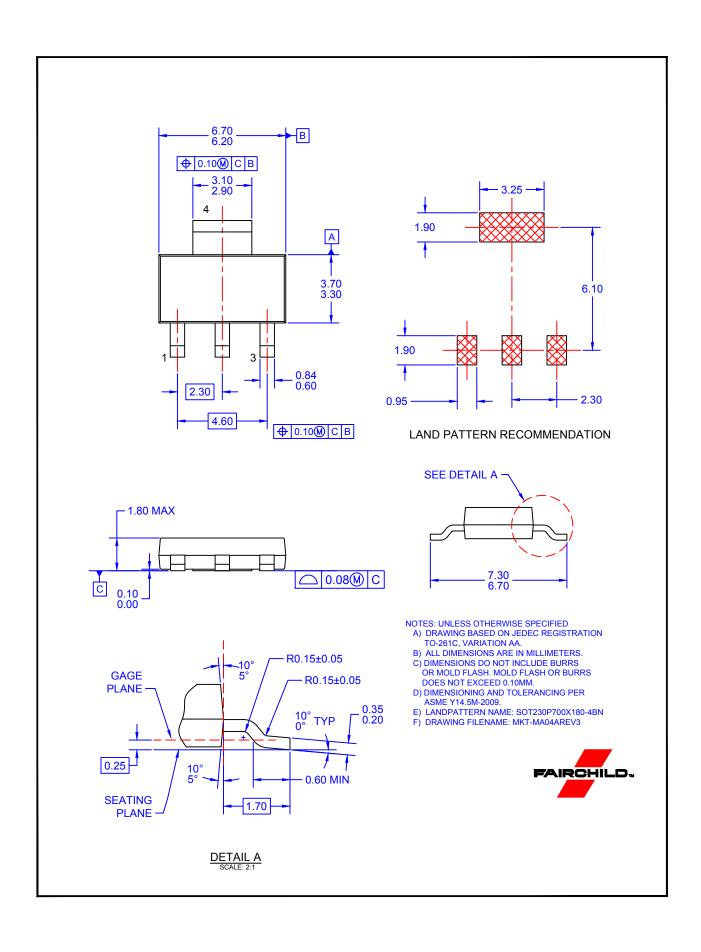


Figure 7. High Frequency Current Gain



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